

# INTERBAND OPTICAL TRANSITIONS IN THE REGION OF EXCITON RESONANCES IN $\text{In}_{0.3}\text{Ga}_{0.7}\text{As}/\text{GaAs}$ QUANTUM WELLS

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Radiation maxima were observed in photoluminescence spectra of  $\text{GaAs}/\text{In}_{0.3}\text{Ga}_{0.7}\text{As}/\text{GaAs}$  in case of 632.8 nm and 532 nm He-Ne laser excitation conditioned by the recombination from ground (e1-hh1, e1-lh1) and excited (e2-hh2, e2-lh2) states of polarionic excitons in quantum wells (fig. 1).

The values of the photoluminescence intensity for  $\text{QW}_A$  and  $\text{QW}_B$  can be affected by various factors that create background fluctuations of the absolute photoluminescence intensity level that are complicating the analysis of the obtained dependences.

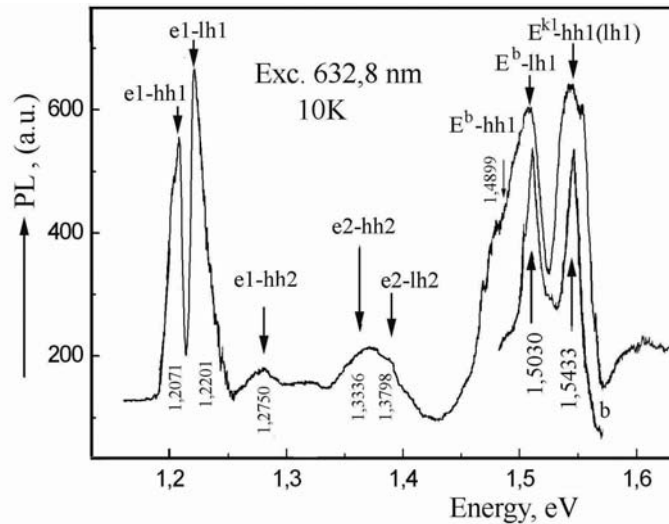


Fig. 1. The luminescence spectra of  $\text{In}_{0.3}\text{Ga}_{0.7}\text{As}/\text{GaAs}$  structure with quantum wells at 10K excited with a 632.8 nm He-Ne laser line (curve b is shown not to scale)

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